优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
60V	50mΩ @ V_{GS} = 10V	18A
	63mΩ @ V_{GS} = 4.5V	16A

Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product

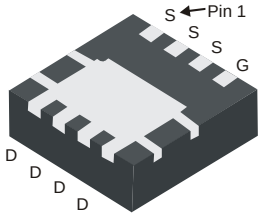
Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

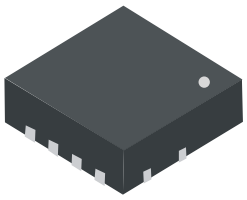
Mechanical Data

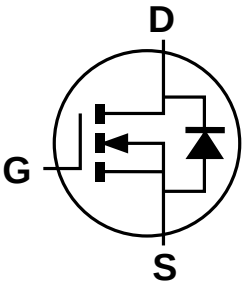
- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.03 grams (Approximate)



Bottom View

PowerDI3333-8


Top View



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	5.6 4.5	A
	Steady State	T_C = +25°C T_C = +70°C	I_D	18 14.5	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I_{DM}	25	A
Maximum Continuous Body Diode Forward Current (Note 7)			I_S	2.5	A
Avalanche Current (Note 8) L = 0.1mH			I_{AS}	12	A
Repetitive Avalanche Energy (Note 8) L = 0.1mH			E_{AS}	7.2	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P_D	0.93	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	134	°C/W
	t<10s		82	
Total Power Dissipation (Note 7)		P_D	2.4	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	53	°C/W
	t<10s		33	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1	μA	V_{DS} = 60V, V_{GS} = 0V
Zero Gate Voltage Drain Current T_J = +150°C	I_{DSS}	—	—	100	μA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	39	50	mΩ	V_{GS} = 10V, I_D = 4.5A
		—	47	63		V_{GS} = 4.5V, I_D = 3A
Diode Forward Voltage	V_{SD}	—	—	1.1	V	V_{GS} = 0V, I_S = 2.5A
On State Drain Current (Note 10)	$I_{D(ON)}$	20	—	—	A	V_{DS} ≧5V, V_{GS} = 10V
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	740	1,480	pF	V_{DS} = 30V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	40	80	pF	
Reverse Transfer Capacitance	C_{rss}	—	28	55	pF	
Gate Resistance	R_g	—	2.2	4	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	6.4	12	nC	V_{DS} = 30V, I_D = 12A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	14	25	nC	
Gate-Source Charge	Q_{gs}	—	2.8	5.5	nC	
Gate-Drain Charge	Q_{gd}	—	2.3	5	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.6	10	ns	V_{DS} = 30V, I_D = 12A, V_{GS} = 10V, R_G = 6.0Ω
Turn-On Rise Time	t_R	—	5.0	10	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	12	24	ns	
Turn-Off Fall Time	t_F	—	3.3	10	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	11	22	ns	I_F = 4.5A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{RR}	—	5.1	10	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

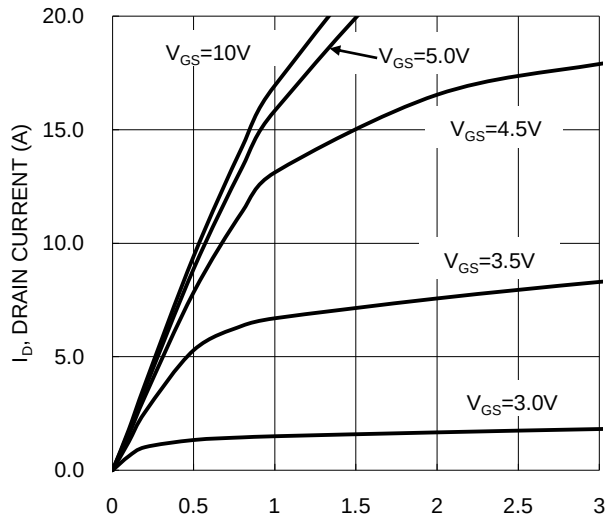


Figure 1. Typical Output Characteristic

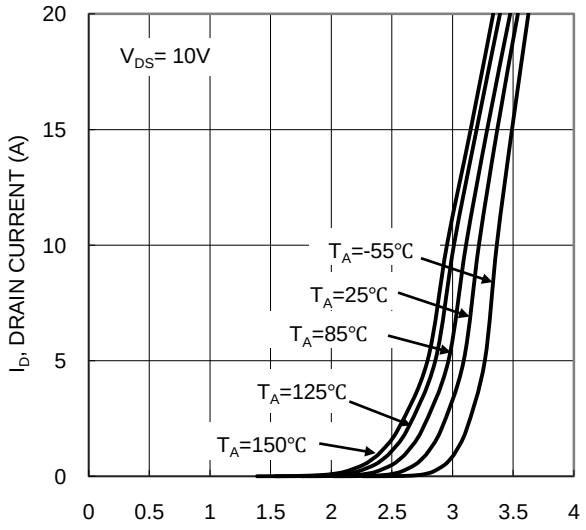


Figure 2. Typical Transfer Characteristic

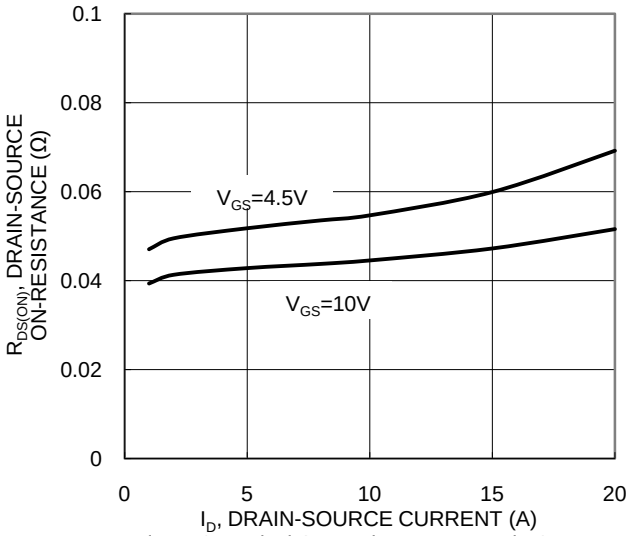


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

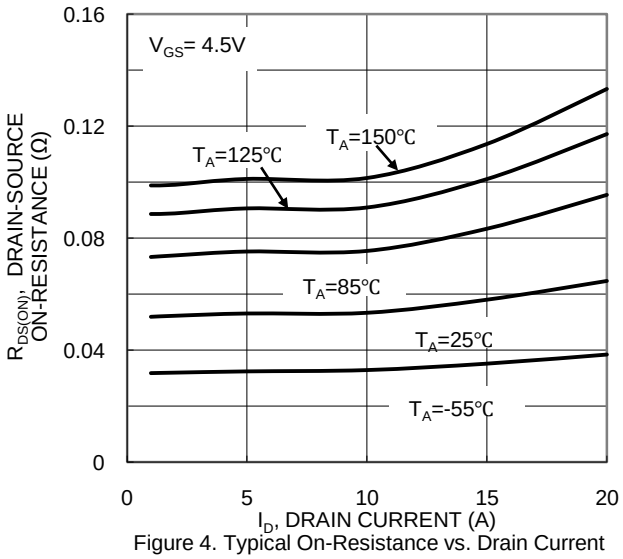


Figure 4. Typical On-Resistance vs. Drain Current and Temperature

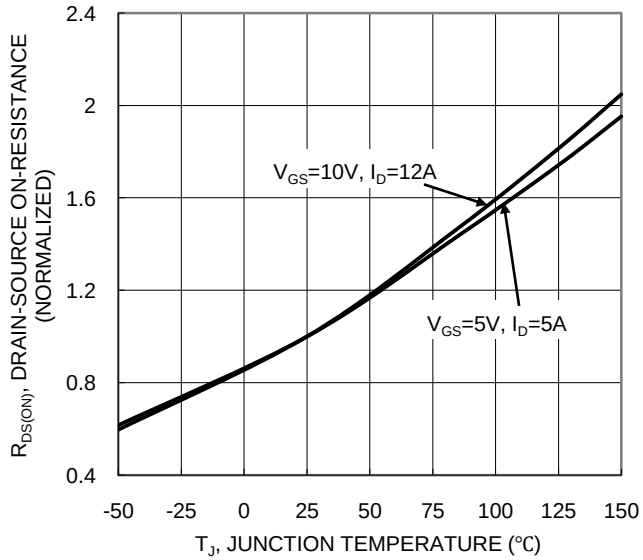


Figure 5. On-Resistance Variation with Temperature

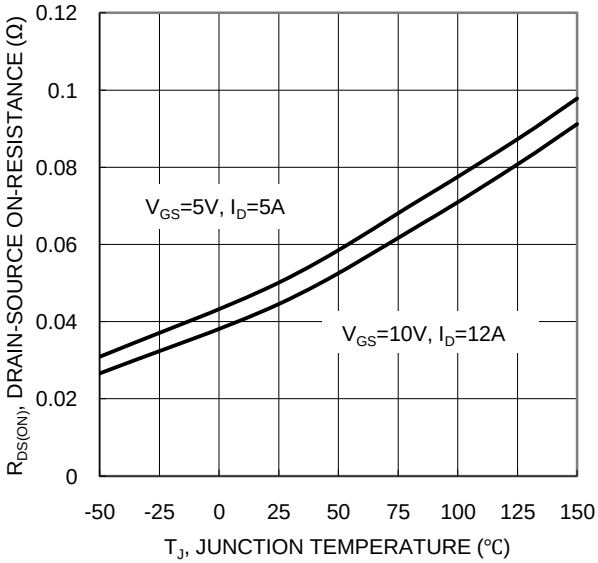


Figure 6. On-Resistance Variation with Temperature

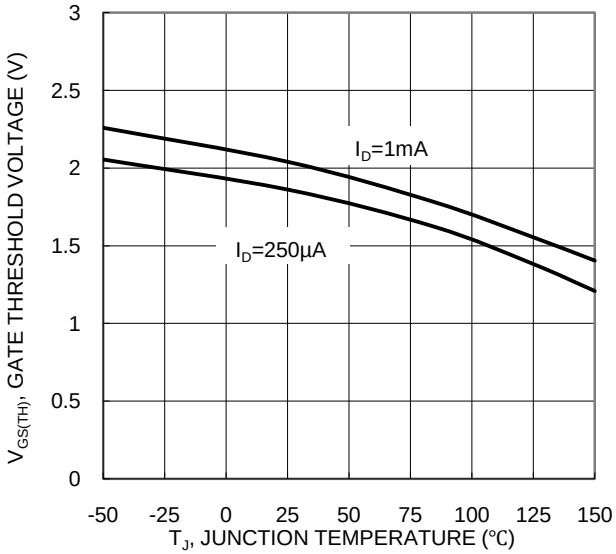


Figure 7. Gate Threshold Variation vs. JunctionTemperature

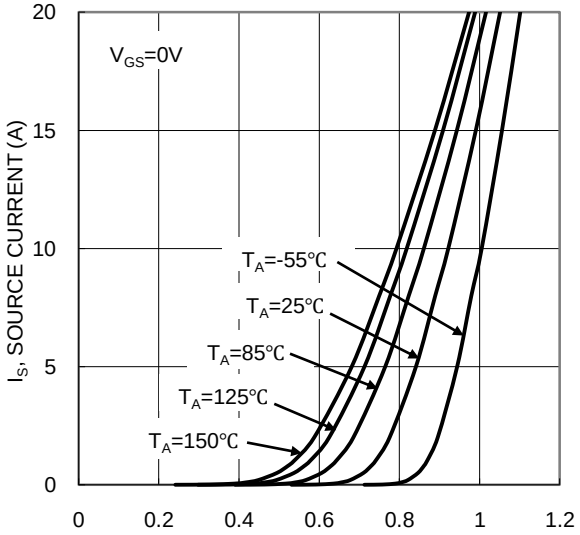


Figure 8. Diode Forward Voltage vs. Current

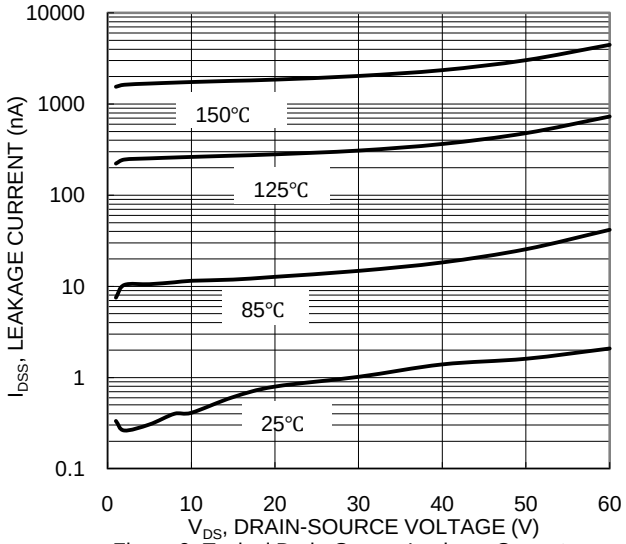


Figure 9. Typical Drain-Source Leakage Current vs. Voltage

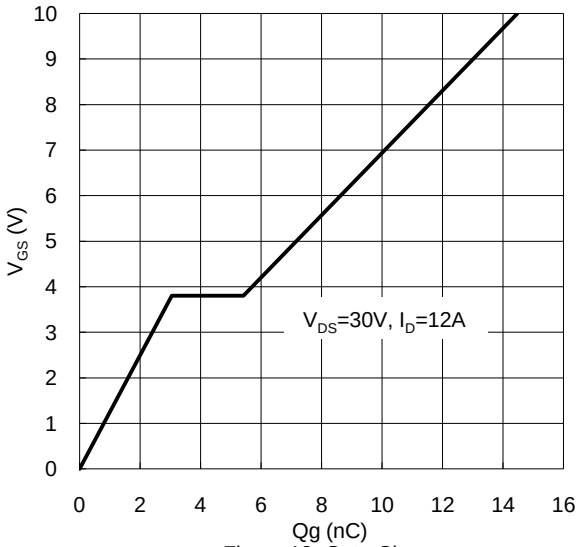


Figure 10. Gate Charge

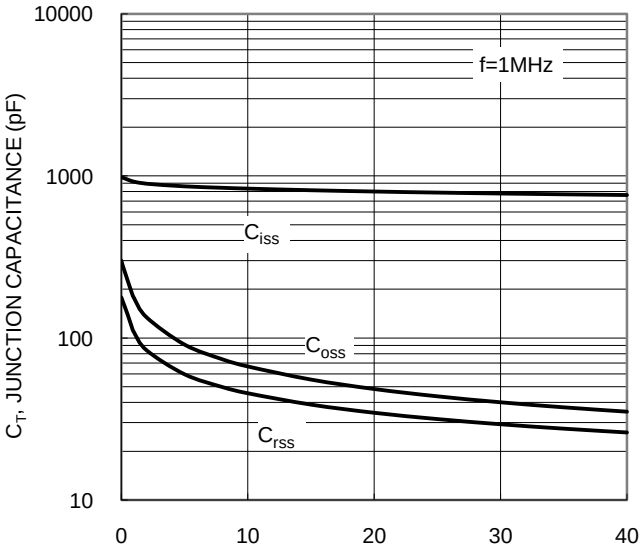


Figure 11. Typical Junction Capacitance

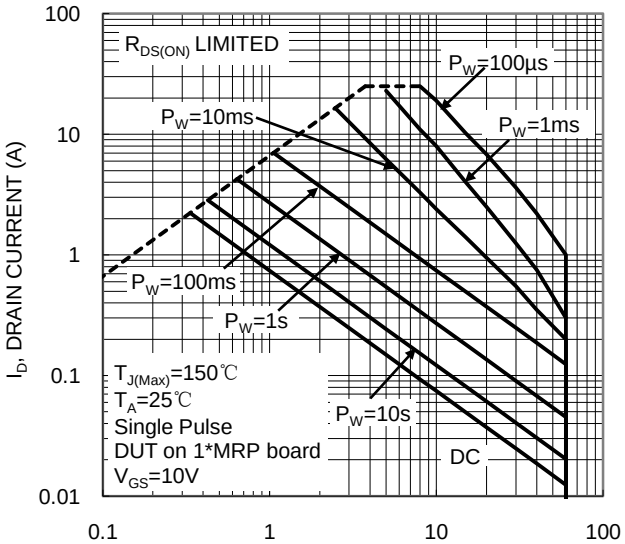


Figure 12. SOA, Safe Operation Area

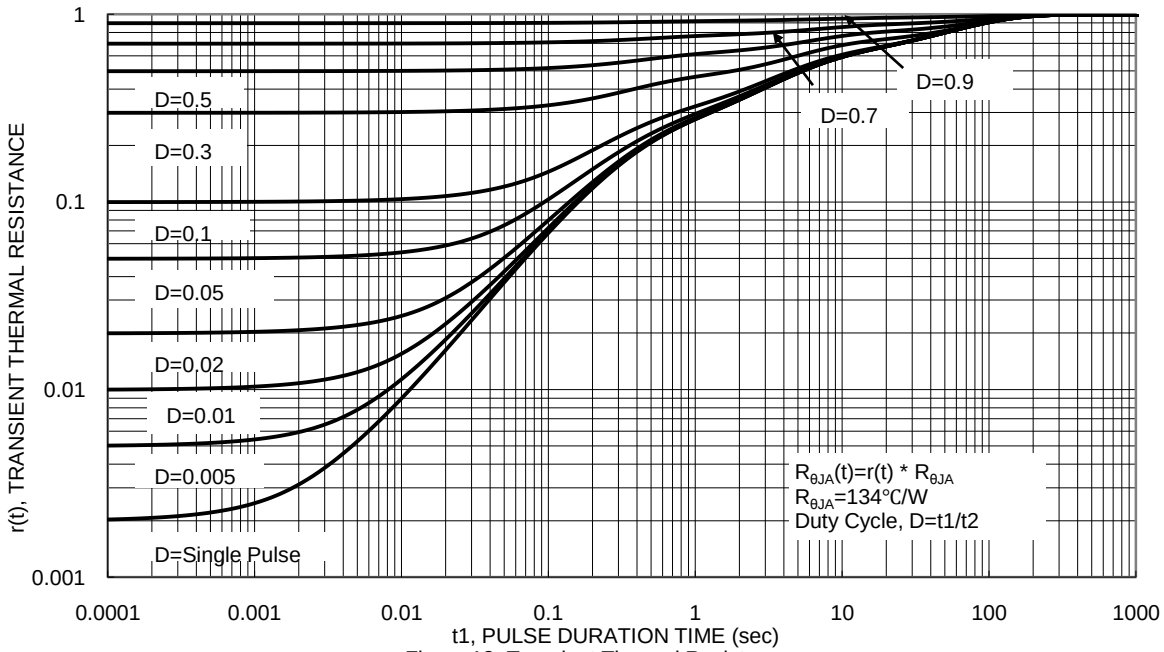
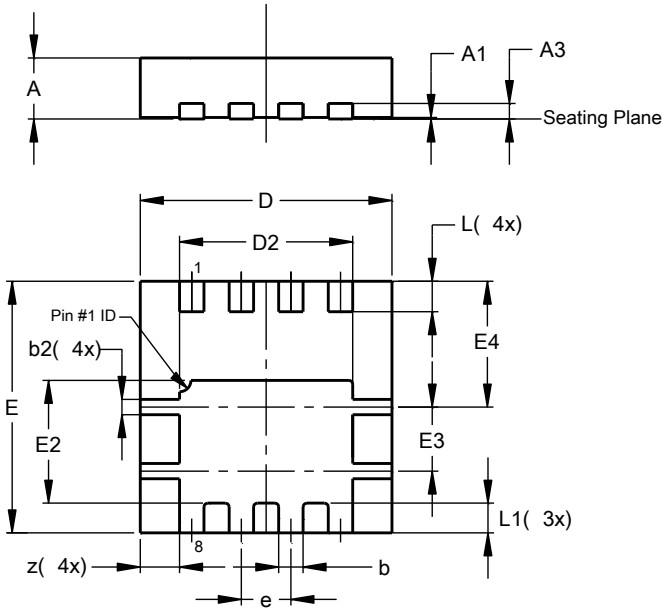


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

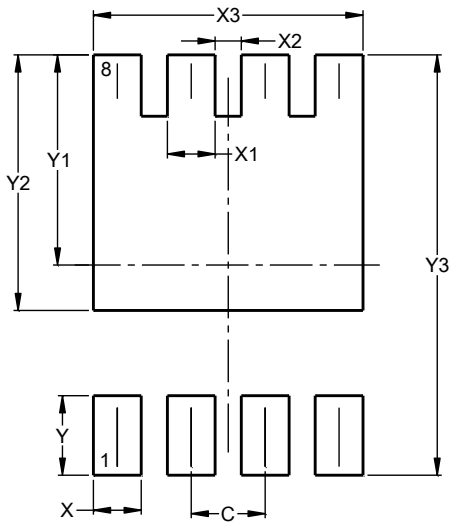
PowerDI3333-8



PowerDI3333-8			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	–	–	0.65
L	0.35	0.45	0.40
L1	–	–	0.39
z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700